Supporting Information

Growth Habits of Bismuth Selenide (Bi$_2$Se$_3$) layers and nanowires over Stranski–Krastanov Indium Arsenide Quantum Dots

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Figure S1. High-resolution Scanning Electron Microscopy (SEM) of the UHD-QDs sample.

Figure S2. Reciprocal space map of the GaAs (002) peak on UHD-QDs sample.
Figure S3. High-resolution HAADF STEM image showing sample with UHD QDs. Arrow indicates approximate location of InAlAs/GaAs interface.

Figure S4. Atomic force microscopy of 32 nm Bi$_2$Se$_3$ layers grown on flat InAs (strained wetting layer).